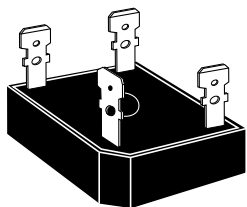


CBR50-020P SERIES
50 AMP
SILICON BRIDGE RECTIFIER
200 thru 1000 VOLTS



CASE FP

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBR50-020P series types are silicon single phase full wave bridge rectifiers designed for general purpose applications. The molded epoxy case has a built in metal baseplate for heat sink mounting.

MARKING CODE: FULL PART NUMBER

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

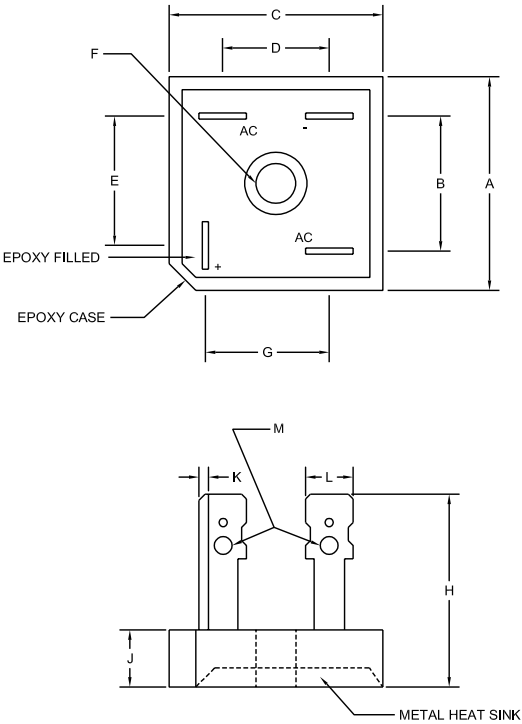
	SYMBOL	CBR50- 020P	CBR50- 040P	CBR50- 060P	CBR50- 080P	CBR50- 100P	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V_R	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	140	280	420	560	700	V
Average Forward Current ($T_C=55^{\circ}\text{C}$)	I_O			50			A
Peak Forward Surge Current	I_{FSM}			400			A
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 to +150			$^{\circ}\text{C}$
Thermal Resistance	θ_{JC}			1.5			$^{\circ}\text{C/W}$
RMS Isolation Voltage (case to lead)	V_{iso}			2500			V_{ac}

ELECTRICAL CHARACTERISTICS PER DIODE ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_R	$V_R=\text{Rated } V_{RRM}, T_C=25^{\circ}\text{C}$		5.0	μA
I_R	$V_R=\text{Rated } V_{RRM}, T_C=125^{\circ}\text{C}$		500	μA
V_F	$I_F=25\text{A}$		1.1	V
C_J	$V_R=4.0\text{V}, f=1.0\text{MHz}$	300		pF

R0 (31-August 2004)

CASE FP - MECHANICAL OUTLINE



R1

**MARKING CODE:
FULL PART NUMBER**

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.115	1.135	28.32	28.83
B	0.692	0.732	17.58	18.59
C	1.115	1.135	28.32	28.83
D	0.542	0.582	13.77	14.78
E	0.632	0.672	16.05	17.07
F (DIA.)	0.200	0.220	5.08	5.59
G	0.632	0.672	16.05	17.07
H	0.740	0.840	18.80	21.34
J	0.290	0.310	7.37	7.87
K	0.030	0.034	0.76	0.86
L		0.250		6.35
M (DIA.)		0.940		2.39

CASE FP (REV:R1)

R0 (31-August 2004)